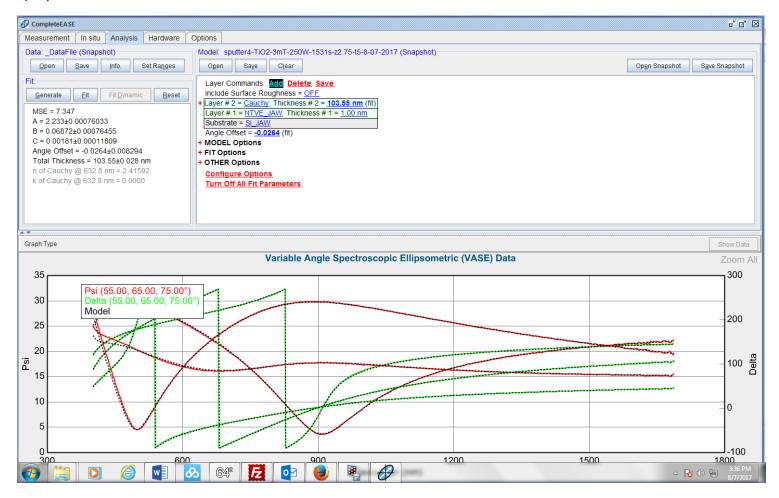
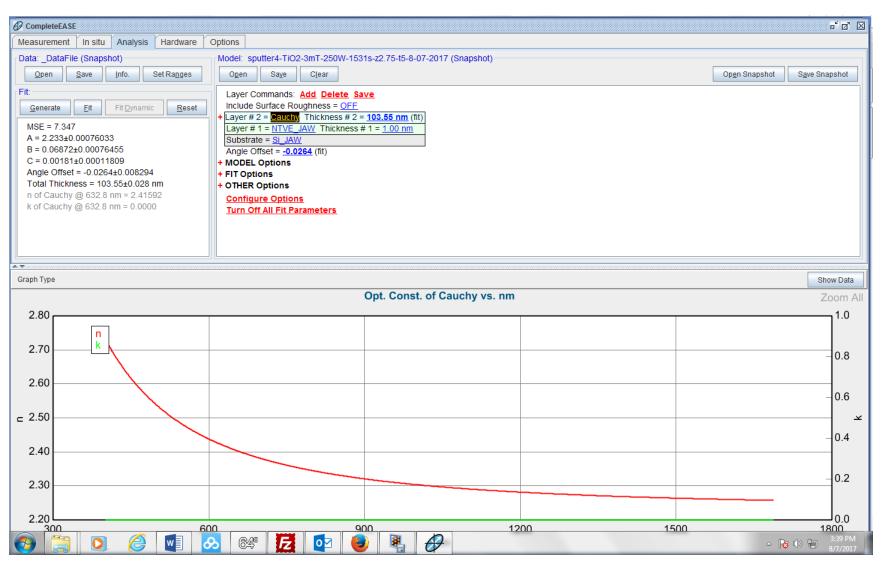
TiO₂ film using Sputter#4

- 1)Film sputtering Condition: Pressure=3mT, RF Power=250 W, O₂/Ar flow-rate=3/45 sccm, z=2.75, Gun tilting=5, rotation=10, and time=1531 s.
- 2) Ellipsometer Measurement: film thickness=103.55 nm.





3)Sheet Resistance: R=23.05x10⁶ Ω /sq, Resistivity=238.7 Ω cm.

4)AFM surface Scan

Figure 1 (a) AFM surface scan of $TiO_2(103.5 \text{ nm})/Si: Ra=0.662 \text{ nm}$; (b) AFM surface scan of Si substrate: Ra=0.208 nm. TiO_2 film roughness Ra=0.454 nm.

